(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

G00002

(43) International Publication Date
22 August 2002 (22.08.2002)

PCT

(10) International Publication Number
WO 02/065528 A3

(51) International Patent Classification[7]: H01L 21/311, 21/768

(21) International Application Number: PCT/US02/03138

(22) International Filing Date: 30 January 2002 (30.01.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/782,446 12 February 2001 (12.02.2001) US

(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538-6470 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **HO, Chok, W.** [US/US]; 372 Meadowhaven Way, Milpitas, CA 95035 (US). **LEE, Chung-Ju** [CN/CN]; 4F, No. 67, Gwang-Cheng Rd., Shung-Thi, Bau-Sun Village, R.O.C. Hsin-Chu (TW). **TANG, Kuo-Lung** [CN/CN]; 9F, No. 310, Lane 1050, Ming-Hu Rd., R.O.C. Hsin-Chu (TW).

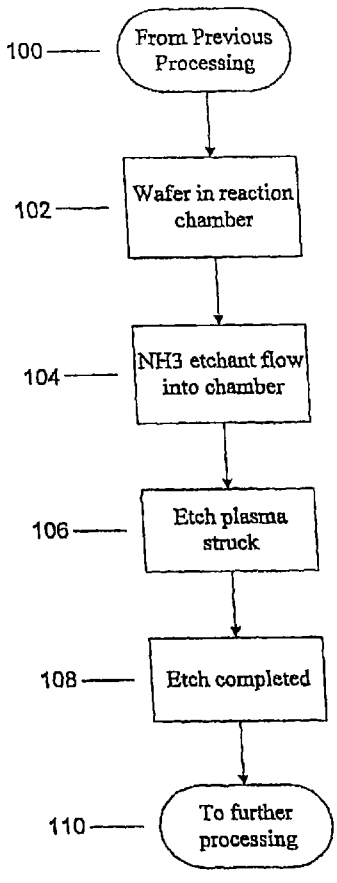
(74) Agent: **OLYNICK, Mary, R.**; Beyer Weaver & Thomas LLP, P.O. Box 778, Berkeley, CA 94704-0778 (US).

(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),

[Continued on next page]

(54) Title: USE OF AMMONIA FOR ETCHING ORGANIC LOW-K DIELECTRICS



(57) Abstract: Method for etching organic low-k dielectric using ammonia, NH3, as an active etchant. Processes using ammonia results in at least double the etch rate of organic low-k dielectric materials than processes using N2/H2 chemistries, at similar process conditions. The difference is due to the much lower ionization potential of NH3 versus N2 in the process chemistry, which results in significantly higher plasma densities and etchant concentrations at similar process conditions.

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European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
13 February 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.